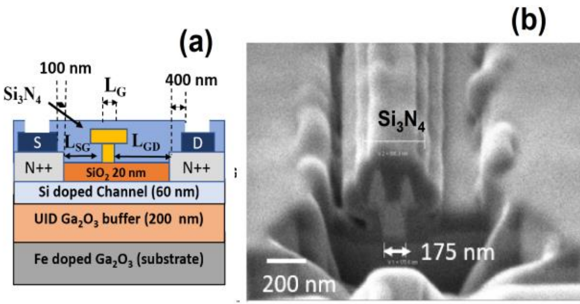


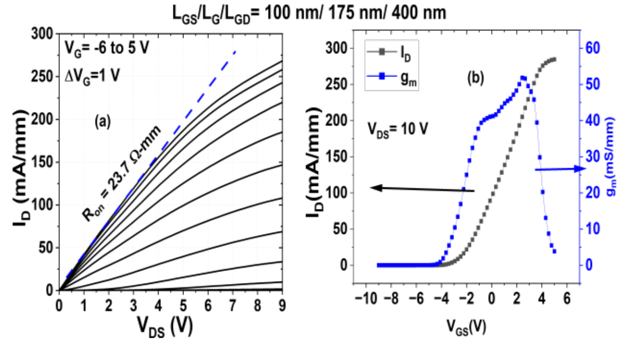
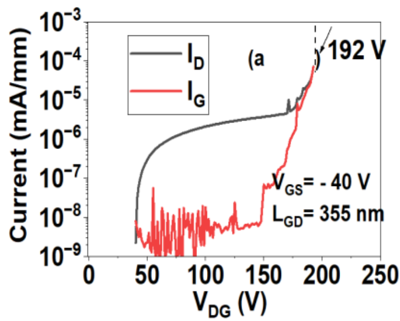
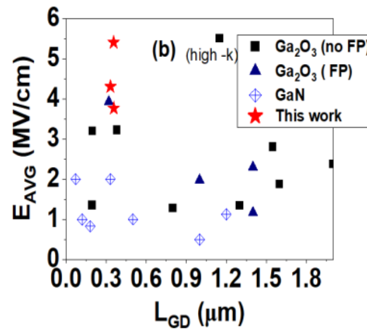


Figure 1(a): Cross section schematic of our fabricated device, (b) FIB cross-section SEM image of a passivated device

Figure 2 (a) Output and (b) transfer curve of a test device





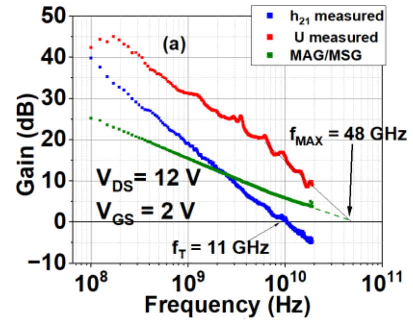
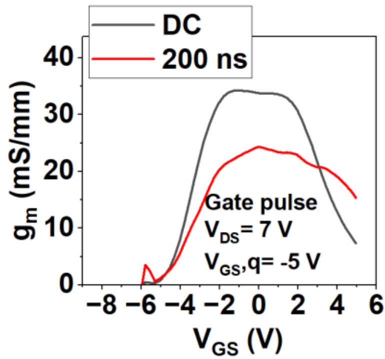


Figure 3 (a) 192 V breakdown voltage recorded for L_{GD}= 355 nm (b) Eavg vs Lgd benchmarking with other Gallium oxide and GaN HEMT devices

Figure 4: small signal analysis showing 48 GHz fmax



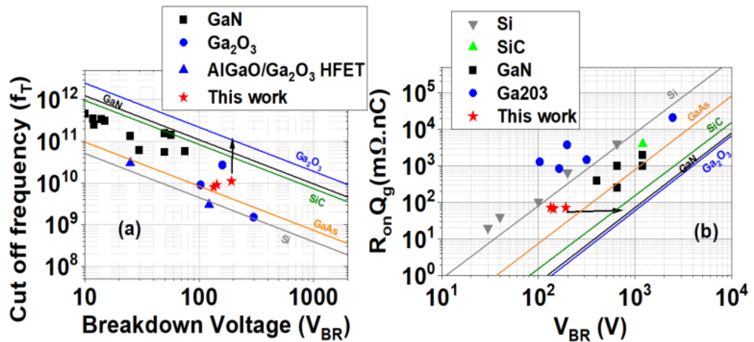


Figure 5: gm measured at 200 ns Showing current collapse for Gate pulse

Figure 6 (a) ft vs Vbr benchmarking of our device, (b) Huang's material figure of merit benchmarking (Ron Qg vs Vbr